

(12) United States Patent
Ghodsi

(10) Patent No.: US 9,627,067 B2
(45) Date of Patent: *Apr. 18, 2017

(54) ERASABLE BLOCK SEGMENTATION FOR MEMORY

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

This patent is subject to a terminal disclaimer.

(21) Appl. No.: 15/082,664

(22) Filed: Mar. 28, 2016

(65) Prior Publication Data

US 2016/0211022 A1 Jul. 21, 2016

Related U.S. Application Data

(63) Continuation of application No. 13/600,591, filed on Aug. 31, 2012, now Pat. No. 9,299,439.

(51) Int. Cl.
GIIC 11/34 (2006.01)
GIIC 16/04 (2006.01)
GIIC 16/14 (2006.01)
GIIC 16/34 (2006.01)

(52) U.S. Cl.
CPC **GIIC 16/0483 (2013.01); GIIC 16/14 (2013.01); GIIC 16/3418 (2013.01)**

(58) Field of Classification Search
CPC .. G11C 16/0483; G11C 16/14; G11C 16/3418
USPC 439/578-585
See application file for complete search history.

(56) References Cited

U.S. PATENT DOCUMENTS

6,262,914 B1	7/2001	Smayling et al.
6,872,640 B1 *	3/2005	Mouli H01L 27/1203 257/347
7,042,765 B2	5/2006	Sibigroth et al.
7,233,024 B2	6/2007	Scheuerlein et al.
7,508,714 B2	3/2009	Fasoli et al.
9,299,439 B2	3/2016	Ghodsi
2012/0069663 A1	3/2012	Itagaki et al.
2012/0176836 A1	7/2012	Iguchi et al.
2014/0063947 A1	3/2014	Ghodsi

* cited by examiner

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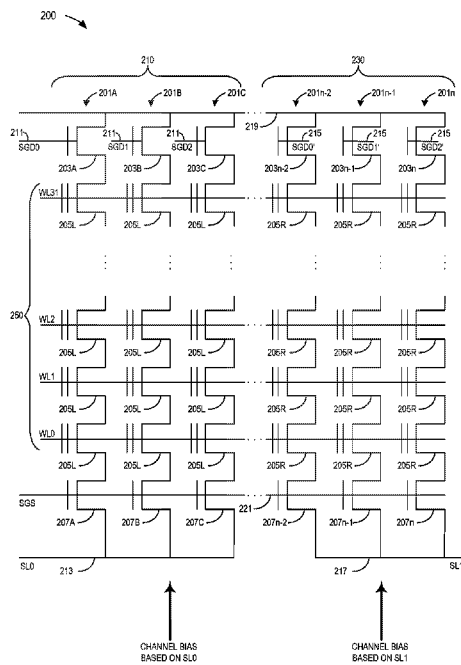
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(57) ABSTRACT

Various embodiments comprise apparatuses such as those having a block of memory divided into sub-blocks that share a common data line. Each of the sub-blocks of the block of memory corresponds to a respective one of a number of segmented sources. Each of the segmented sources is electrically isolated from the other segmented sources of the block of memory. Additional apparatuses and methods of operation are described.

26 Claims, 5 Drawing Sheets



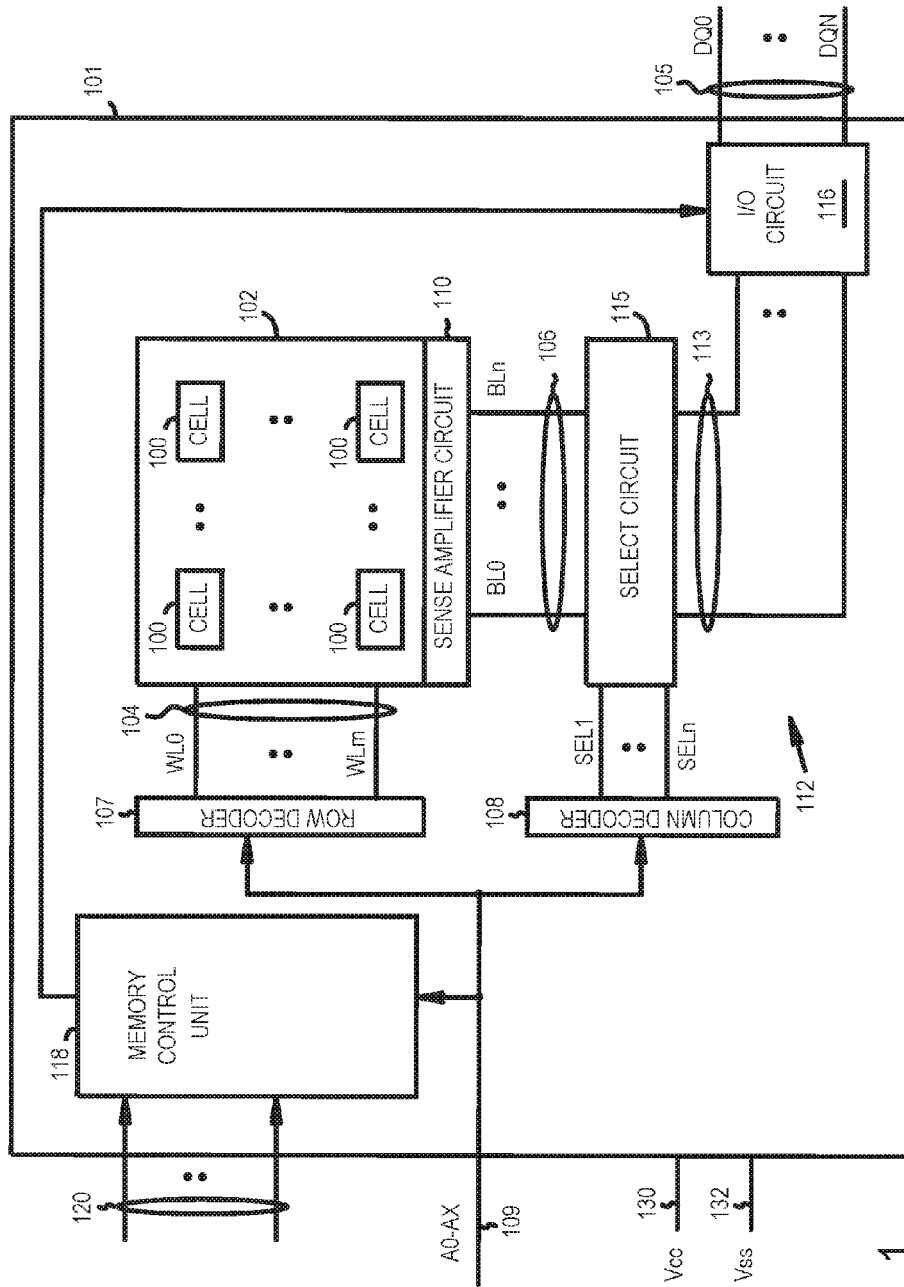


FIG. 1

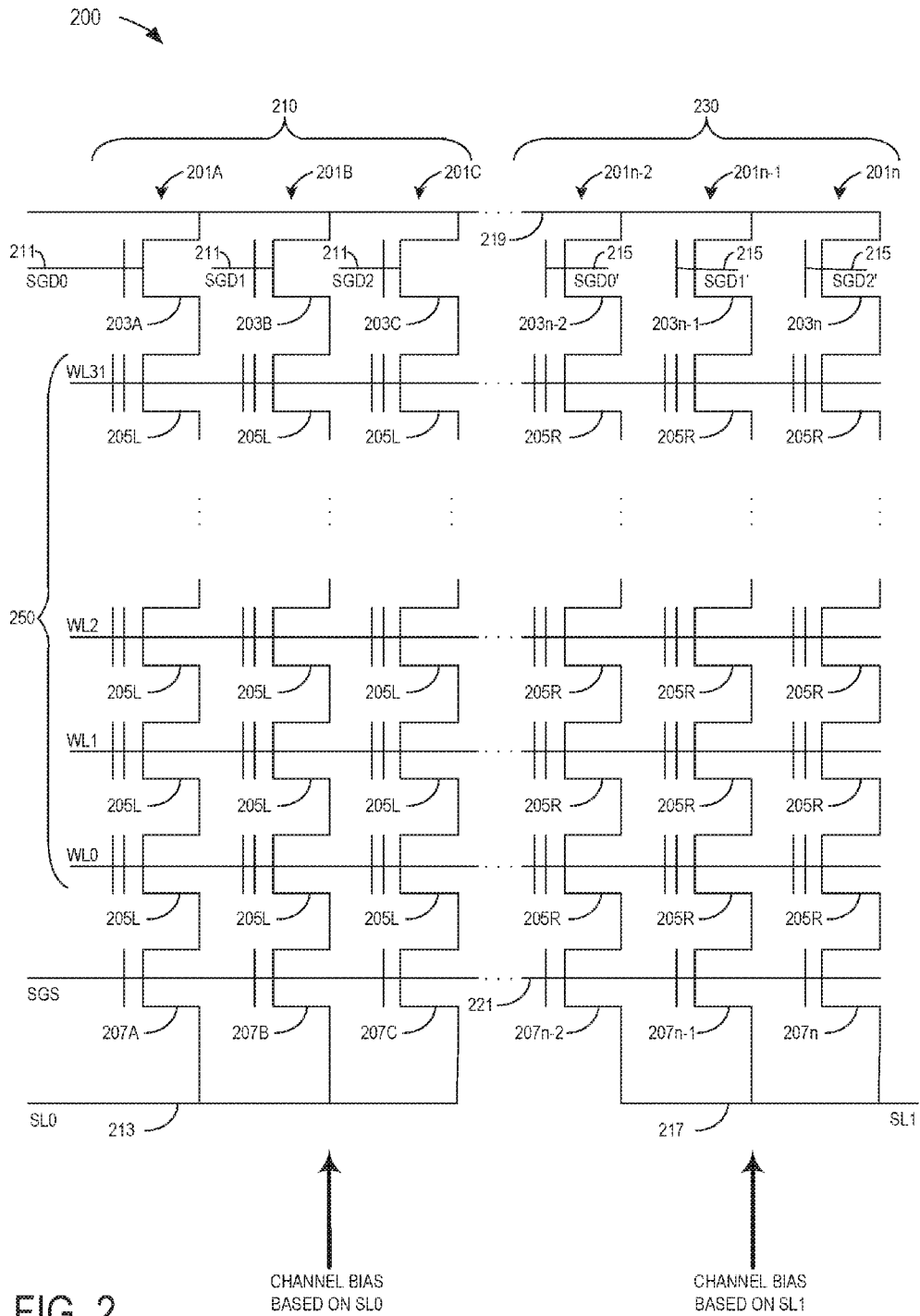


FIG. 2

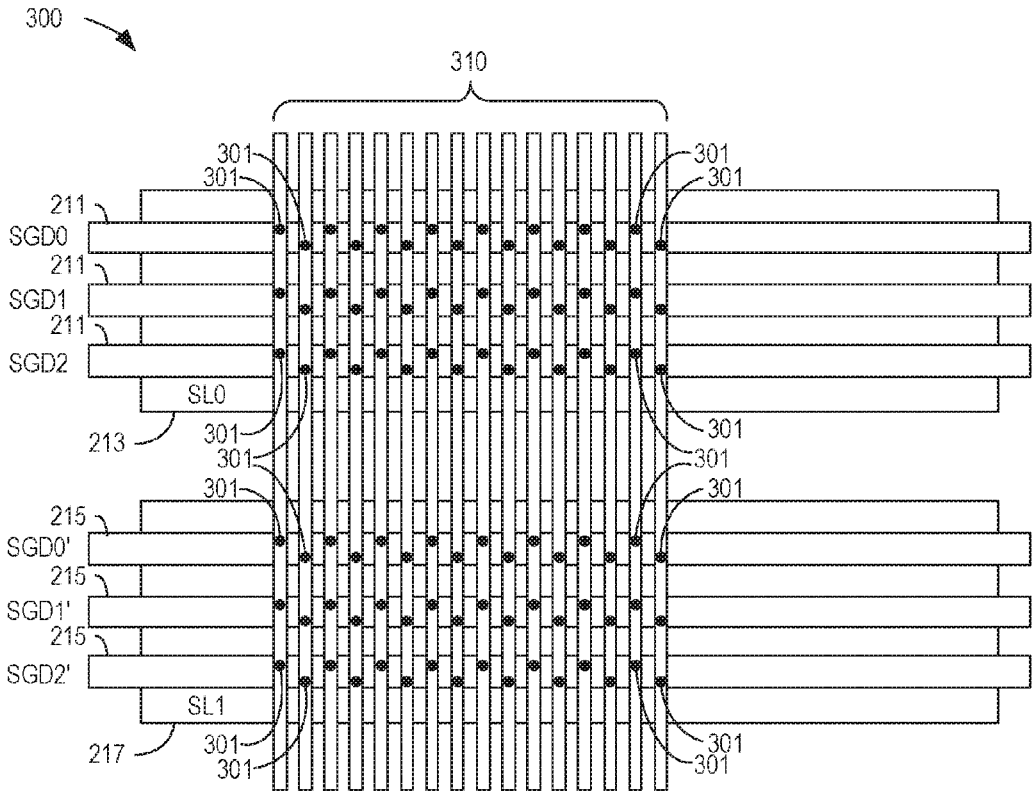


FIG. 3

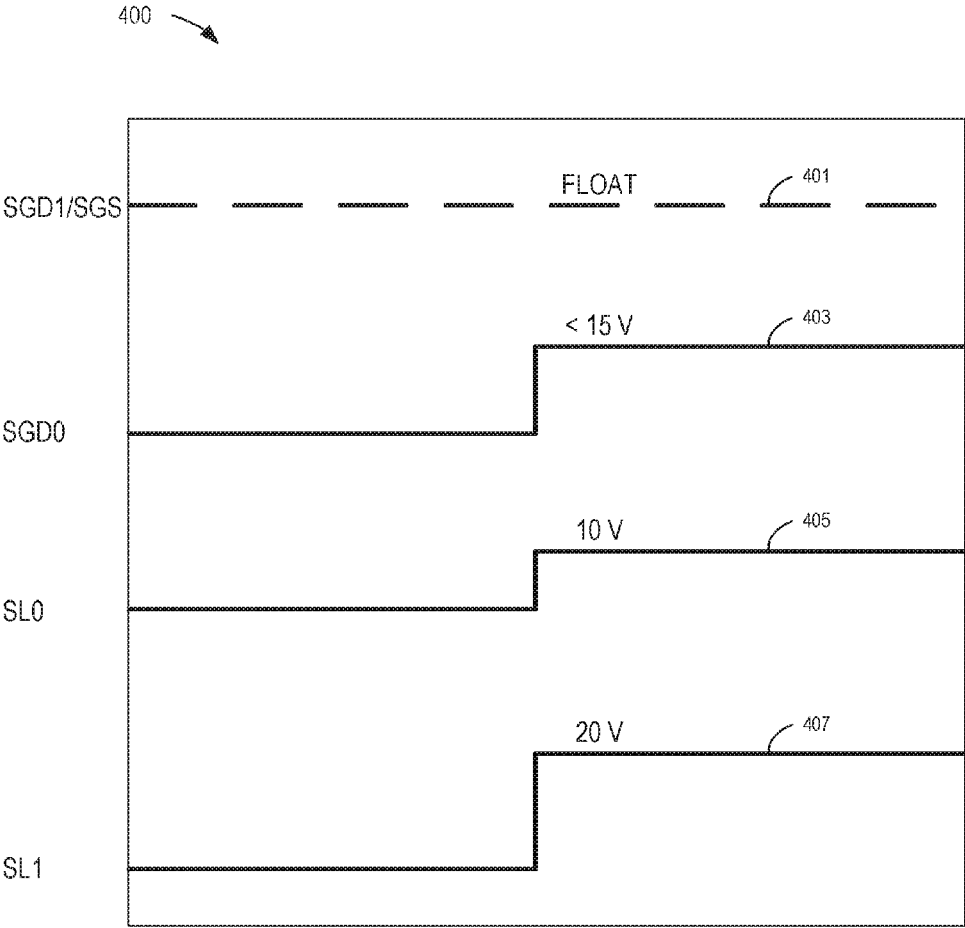


FIG. 4

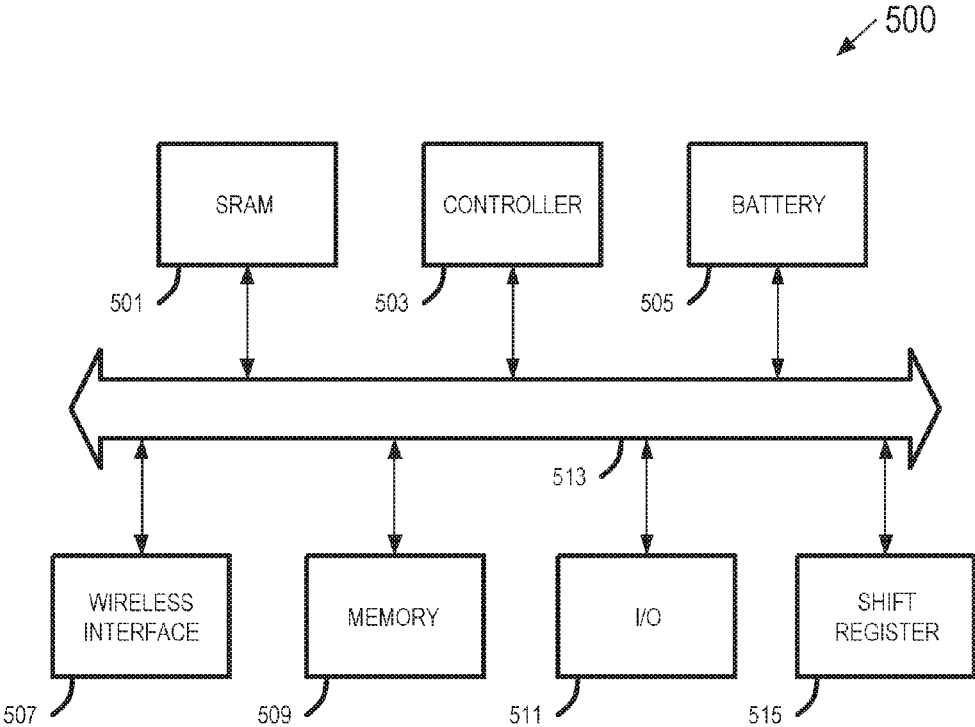


FIG. 5

ERASABLE BLOCK SEGMENTATION FOR MEMORY

PRIORITY APPLICATION

This application is a continuation of U.S. application Ser. No. 13/600,591, filed Aug. 31, 2012, and now issued as U.S. Pat. No. 9,299,439, which is incorporated herein by reference in its entirety.

BACKGROUND

Computers and other electronic systems, for example, digital televisions, digital cameras, and cellular phones, often have one or more memory devices to store information. Increasingly, memory devices are being reduced in size to achieve a higher density of storage capacity. Even when increased density is achieved, consumers often demand that memory devices also use less power while maintaining high speed access.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a block diagram of a memory device having a memory array with memory cells, according to an embodiment;

FIG. 2 is a simplified schematic diagram of a portion of a memory block having segmented sources, according to various embodiments;

FIG. 3 is a plan view of the portion of the memory block of FIG. 2, showing an example of erasable sub-blocks of the memory;

FIG. 4 is a graph of bias conditions that may exist within the memory block of FIG. 3; and

FIG. 5 is a block diagram of a system embodiment, including a memory device.

DETAILED DESCRIPTION

The description that follows includes illustrative apparatuses (circuitry, devices, structures, systems, and the like) and methods (e.g., processes, sequences, techniques, and technologies) that embody the subject matter. In the following description, for purposes of explanation, numerous specific details are set forth in order to provide an understanding of various embodiments of the subject matter. After reading this disclosure, it will be evident to those of ordinary skill in the art however, that various embodiments of the subject matter may be practiced without these specific details. Further, well-known apparatuses and methods have not been shown in detail so as not to obscure the description of various embodiments.

To increase the density of a memory device, memory designers consider the area (e.g., footprint) on an underlying substrate for a memory cell. A memory cell may be defined by a feature size, F , where F is the minimum feature size due to various processing limitations, such as lithography limitations, including the numerical aperture and wavelength of the photolithographic systems employed. The memory cell area may have dimensions of $2F$ by $2F$, or $4F^2$. In some two-dimensional NAND memory structures, only one memory cell resides in a $4F^2$ area. In a three-dimensional (3D) NAND memory structure, there may be N tiers (e.g., layers) of memory cells where the memory cells are stacked, one above another, to form the N tiers. Therefore, in these

structures, each memory cell may still be defined by the $4F^2$ area. However, there are N memory cells within that area due to the 3D structure.

To further illustrate, a NAND string of memory cells is formed between a source (e.g., a source line, source slot, or source diffusion region) and a data line as is known independently in the art. A block of memory is comprised of a number of pages. The block is the smallest chunk of memory that a user can erase at one time. Contemporaneous devices may have, for example, 32 kilobytes erasable by a common source and a single data line. In a two-dimensional (e.g., planar) memory array, a single block may have two to four megabytes of memory. A 3D memory array may occupy the same area on the substrate but have a much higher density. For example, the block size can be between eight and 16 megabytes, or higher, for the same sized area on the substrate of a two-dimensional memory array. Thus, the 3D memory density can be four times the memory of the two-dimensional array. Consequently, the block size in a 3D memory array is usually larger than the 2D memory array.

One detrimental side effect of this increase in memory density for the same area on the substrate is that the number of simultaneously erasable pages of memory in a block is also increased. For example, if the number of tiers in the 3D NAND memory array is doubled, the number of pages per block can quadruple. In many applications, the increase in block size is inconvenient or even intolerable. Thus, the various embodiments described herein reduce the erasable block size.

In various embodiments described herein, smaller erasable blocks can be achieved by segmenting the global sources and drain select lines within each physical block. Segmentation of the global source allows an erase operation to be limited to one or more selected sub-blocks. The segmented drain select lines are formed to correspond with segmented source lines within each sub-block.

Further, junctions at either end of the NAND string connected to select gate, source-side (SGS) or select gate drain-side (SGD) devices can be designed to have different breakdown voltage depending on which junction is used to initiate the needed erase voltage in the NAND string. For example, if the SGS device is used to initiate the erase voltage then one can design its breakdown voltage to be lower than the SGD device junction. The higher SGD breakdown voltage should help prevent an erase disturb of memory cells in adjacent non-selected sub-blocks by preventing the developed erase voltage to be transmitted to adjacent sub blocks. Examples of erase bias conditions are also described herein to implement the erase operation within individual sub-blocks.

Referring now to FIG. 1, a block diagram of an apparatus in the form of a memory device **101** is shown. The memory device **101** includes one or more memory arrays **102** having a number (e.g., one or more) of memory cells **100** according to an embodiment. The memory cells **100** can be arranged in rows and columns along with access lines **104** (e.g., word-lines to conduct signals WL_0 through WL_m) and first data lines **106** (e.g., bit lines to conduct signals BL_0 through BL_n). The memory device **101** can use the access lines **104** and the first data lines **106** to transfer information to and from the memory cells **100**. A row decoder **107** and a column decoder **108** decode address signals A_0 through A_X on address lines **109** to determine which ones of the memory cells **100** are to be accessed.

Sense circuitry, such as a sense amplifier circuit **110**, operates to determine the values of information read from the memory cells **100** in the form of signals on the first data

lines 106. The sense amplifier circuit 110 can also use the signals on the first data lines 106 to determine the values of information to be written to the memory cells 100.

The memory device 101 is further shown to include circuitry 112 to transfer values of information between the memory array 102 and input/output (I/O) lines 105. Signals DQ0 through DQn on the I/O lines 105 can represent values of information read from or to be written into the memory cells 100. The I/O lines 105 can include nodes of the memory device 101 (e.g., pins, solder balls, or other interconnect technologies such as controlled collapse chip connection (C4), or flip chip attach (FCA)) on a package where the memory device 101 resides. Other devices external to the memory device 101 (e.g., a memory controller or a processor, not shown in FIG. 1) can communicate with the memory device 101 through the I/O lines 105, the address lines 109, or the control lines 120.

The memory device 101 can perform memory operations, such as a read operation, to read values of information from selected ones of the memory cells 100 and a programming operation (also referred to as a write operation) to program (e.g., to write) information into selected ones of the memory cells 100. The memory device 101 can also perform a memory erase operation to clear information from some or all of the memory cells 100.

A memory control unit 118 controls memory operations using signals on the control lines 120. Examples of the signals on the control lines 120 can include one or more clock signals and other signals to indicate which operation (e.g., a programming operation or read operation) the memory device 101 can or should perform. Other devices external to the memory device 101 (e.g., a processor or a memory controller) can control the values of the control signals on the control lines 120. Specific combinations of values of the signals on the control lines 120 can produce a command (e.g., a programming, read, or erase command) that can cause the memory device 101 to perform a corresponding memory operation (e.g., a program, read, or erase operation).

Although various embodiments discussed herein use examples relating to a single-bit memory storage concept for ease in understanding, the inventive subject matter can be applied to numerous multiple-bit schemes as well. For example, each of the memory cells 100 can be programmed to a different one of at least two data states to represent, for example, a value of a fractional bit, the value of a single bit or the value of multiple bits such as two, three, four, or a higher number of bits.

For example, each of the memory cells 100 can be programmed to one of two data states to represent a binary value of "0" or "1" in a single bit. Such a cell is sometimes called a single-level cell (SLC).

In another example, each of the memory cells 100 can be programmed to one of more than two data states to represent a value of, for example, multiple bits, such as one of four possible values "00," "01," "10," and "11" for two bits, one of eight possible values "000," "001," "010," "011," "100," "101," "110," and "111" for three bits, or one of another set of values for larger numbers of multiple bits. A cell that can be programmed to one of more than two data states is sometimes referred to as a multi-level cell (MLC). Various operations on these types of cells are discussed in more detail, below.

The memory device 101 can receive a supply voltage, including supply voltage signals V_{cc} and V_{ss} , on a first supply line 130 and a second supply line 132, respectively. Supply voltage signal V_{ss} can, for example, be at a ground

potential (e.g., having a value of approximately zero volts). Supply voltage signal V_{cc} can include an external voltage supplied to the memory device 101 from an external power source such as a battery or alternating-current to direct-current (AC-DC) converter circuitry (not shown in FIG. 1).

The circuitry 112 of the memory device 101 is further shown to include a select circuit 115 and an input/output (I/O) circuit 116. The select circuit 115 can respond to signals SEL1 through SELn to select signals on the first data lines 106 and the second data lines 113 that can represent the values of information to be read from or to be programmed into the memory cells 100. The column decoder 108 can selectively activate the SEL1 through SELn signals based on the A0 through AX address signals present on the address lines 109. The select circuit 115 can select the signals on the first data lines 106 and the second data lines 113 to provide communication between the memory array 102 and the I/O circuit 116 during read and programming operations.

The memory device 101 may comprise a non-volatile memory device, and the memory cells 100 can include non-volatile memory cells, such that the memory cells 100 can retain information stored therein when power (e.g., V_{cc} , or V_{ss} , or both) is disconnected from the memory device 101.

Each of the memory cells 100 can include a memory element having material, at least a portion of which can be programmed to a desired data state (e.g., by being programmed to a corresponding charge storage state). Different data states can thus represent different values of information programmed into each of the memory cells 100.

The memory device 101 can perform a programming operation when it receives (e.g., from an external processor or a memory controller) a programming command and a value of information to be programmed into one or more selected ones of the memory cells 100. Based on the value of the information, the memory device 101 can program the selected memory cells to appropriate data states to represent the values of the information to be stored therein.

One of ordinary skill in the art may recognize that the memory device 101 may include other components, at least some of which are discussed herein. However, several of these components are not shown in the figure, so as not to obscure details of the various embodiments described. The memory device 101 may include devices and memory cells, and operate using memory operations (e.g., programming and erase operations) similar to or identical to those described below with reference to various other figures and embodiments discussed herein.

With concurrent reference now to FIG. 2 and FIG. 3, a simplified schematic diagram of a portion of a memory block 200 having sub-blocks, according to various embodiments, is shown. FIG. 3 shows a plan view 300 of the schematic diagram of FIG. 2.

For ease in understanding the subject matter, only one portion of a three-dimensional memory structure is shown. As will be apparent to a person of ordinary skill in the art, the portion of the memory block 200 may be one portion of a block formed substantially normal to a face of an underlying substrate on which the memory is formed. For example, NAND memory cell strings are arranged substantially perpendicular relative to a face of the substrate. Conventional 3D memory structures are known independently in the art.

The portion of the memory block 200 includes a left-side sub-block 210 and a right-side sub-block 230. However, the disclosed subject matter is not limited to left and right sub-blocks. Sub-blocks may be arranged in various configura-

rations and include varying numbers of strings of memory cells. The number of sub-blocks may be in the hundreds or more, depending on the size of the memory block and the number of strings per sub-block. Additionally, the various embodiments described herein may be used with various types of electronic devices.

Each of the left-side sub-block **210** and the right-side sub-block **230** include a number of NAND memory cell strings **201A**, **201B**, . . . , **201n**. A common bit line **219** is coupled to each of the strings. Although the illustrated portion of the memory block **200** shows only one bit line and six memory cell strings for ease of illustration and discussion, a block typically includes many more bit lines and memory cell strings. The NAND memory cell strings **201A**, **201B**, **201C** in the left-side sub-block **210** each include a number of memory cells **205L**. Similarly, each of the NAND memory cell strings **201n-2**, **201n-1**, **201n** in the right-side sub-block **230** includes a number of memory cells **205R**. Each of the sub-blocks therefore comprises a number of non-overlapping ones of the memory cell strings **201**. For example, the non-overlapping strings indicate that each memory cell/string is only contained within one sub-block. Therefore, no sub-blocks share a memory cell/string.

Each end of the NAND memory cell strings **201A**, **201B**, **201C** in the left-side sub-block **210** is coupled to one of a left-side drain select device **203A**, **203B**, **203C** and a left-side source select device **207A**, **207B**, **207C**. Each end of the NAND memory cell strings **201n-2**, **201n-1**, **201n** in the right-side sub-block **230** is coupled to one of a right-side drain select device **203n-2**, **203n-1**, **203n** and a right-side source select device **207n-2**, **207n-1**, **207n**. Each gate on the source select devices **207A** . . . **207n** is coupled to a common source select (SGS) line **221**.

The left-side sub-block **210** and the right-side sub-block **230** each include a separate set of drain select devices. The left-side sub-block **210** has left-side drain select devices **203A**, **203B**, **203C**. The right-side sub-block **230** has right-side drain select devices **203n-2**, **203n-1**, **203n**. Gates of the left-side drain select devices **203A**, **203B**, **203C** are each coupled separately to left-side select gate on drain side (SGD) lines **211** that can receive signals **SGD0**, **SGD1**, **SGD2**, respectively, while gates of the right-side drain select devices **203n-2**, **203n-1**, **203n** are each coupled separately to right-side SGD lines **215**, that can receive signals **SGD0'**, **SGD1'**, **SGD2'**, respectively. Separate bias level may be applied to each of the left-side SGD lines **211** and the right-side SGD lines **215**.

Further, each of the left-side sub-block **210** and the right-side sub-block **230** has a separate segmented source; a left-side source **213** and a right-side source **217**. The left-side source **213** and a right-side source **217** can therefore be biased with separate bias signals, **SL0** and **SL1**, respectively. Consequently, a separate bias level may be applied to each of the left-side source **213** and a right-side source **217**. Examples of various bias signals as they might exist within the memory block **200** are described below with reference to FIG. 4.

Thus, the SGD lines and the source are segmented within the block, with each of the segmented sources **213**, **217** of the block corresponding to a respective one of a number of sub-blocks. For example, each portion of the memory block **200** comprising a sub-block has physically segmented sources and drain select lines. Since the sources and drain select lines are physically segmented, the segmented source in one sub-block is electrically isolated from the segmented sources in other sub-blocks. In various embodiments, bit lines, word lines, and source select lines are shared in

common between sub-blocks. In other embodiments, the bit lines, word lines, and source select lines may be segmented between sub-blocks.

The portion of the memory block **200** also shows a number of word lines **250**. Although the figure indicates there are a total of 32 word lines, the exact number of word lines is irrelevant to the disclosed subject matter. Any higher number or lower number of word lines may be used with the various embodiments described herein. As is evident to a person of ordinary skill in the art, lines labeled **WL** and the bit line **219** in FIG. 2 may correspond to any one of the access lines **104** and any one of the first data lines **106** of FIG. 1, respectively.

Referring now to FIG. 3, the plan view **300** of the memory block **200** of FIG. 2 indicates a number of data lines **310** (e.g., bit lines) coupled at points **301** to pillars within each NAND memory cell strings **201A**, **201B**, . . . , **201n**. The points **301** may also be considered a connection point from the NAND memory cell strings to selected ones of the data lines **310**. Although the figure indicates **16** data lines (e.g., bit lines), the exact number of word lines is irrelevant to the disclosed subject matter. Any higher or lower numbers of data lines may be used with the various embodiments described herein.

The arrangements shown, by way of example, in FIG. 2 and FIG. 3, allow creating erasable sub-blocks without the need to segment the data lines **310** and create independent banks of data lines and associated circuitry (e.g., independent sense circuitry). The creation of independent banks of data lines and associated circuitry would otherwise result in a significant increase in cost and a commensurate increase in area (e.g., footprint) of the memory device. As discussed herein, a lower SGD junction breakdown relative to the SGS junction breakdown can prevent an erase voltage initiated by one source to propagate to the other sub-block via the data lines.

FIG. 4 is a graph **400** of bias conditions that may exist within the memory block of FIG. 2. In FIG. 4, an example of signals that can be applied to erase the memory cells **205R** in the right-side sub-block **230** while attempting to prevent an erase or erase disturb to the memory cells **205L** in the left-side sub-block **210** is shown. When the mechanisms described herein are not used, an erase signal applied within one of the sub-blocks selected for an erase operation may cause an erase disturb, or possibly a complete erasing, of the memory cells in the other non-selected sub-block.

As described previously, the portion of the memory block **200** has physically segmented sources **213**, **217** and drain select lines for the sub-blocks **210**, **230**. The **SL1** signal on the right-side source **217** causes current to flow through the channel of each of the memory cells **205R** in the NAND memory cell strings **201** in the right-side sub-block **230**, raising the channel potential of strings attached to **SL1** in FIG. 2. However, a reverse junction bias condition in the left-side drain select devices **203A**, **203B**, **203C** may allow current to flow from the bit line **219** to the memory cells **205L** in the left-side sub-block **210**. Consequently, the memory cells **205L** in the non-selected left-side sub-block **210** should be protected to prevent an unintentional erase or erase disturb.

With reference again to FIG. 4, the graph **400** indicates that the SGD lines coupled to the SGD devices **203** of the selected right-side sub-block **230**, and SGS line **221**, are allowed to float. A bias level **407** (**SL1**) applied to segmented source **217** of the selected right-side sub-block **230**, is raised to 20 V while a bias level **405** (**SL0**) of 10 V is applied to segmented source **213**. The bias level **407** at 20 V is

sufficient to allow erasure of the memory cells **205L** in the right-side sub-block **230**. However, the bias level **407** (SL0) at 10 V prevents (or at least substantially reduces) the unintentional erasure of the memory cells **205R**. The bias level **407** (SL0) at 10 V may prevent the SGD junctions connected to the common data lines from reaching sufficient breakdown voltage levels to cause a leak back from the data line to channels of the memory cells **205L**. This can be achieved by initially setting the channel potential in devices on the left side to some intermediate levels (e.g., a level not high enough to cause an erase disturb). Initializing SL0 to a voltage around 10 V (e.g., between about 0 V to about 10 V, in general) initializes the channel in the left side to a higher intermediate potential thereby reducing the SGD junction potential on the data line side when SL1 is raised to 20V.

Keeping the bias level **403** on the drain select lines **211** coupled to the SGD device **203A**, for example, at an SGD0 value no more than 15 V (or approximately 75% of the bias level **407** applied to segmented source **217**), prevents gate oxide breakdown to occur in left side SGD devices and help the reverse bias condition discussed above not to occur. This prevents the voltage on the bit line **219** causing an erase disturb in the memory cells **205L**. Ensuring that the SGD junction breakdown voltage is less than the SGS junction breakdown, only approximately 10 V (in this example) is another important design feature preventing BL voltage transfer to **205L** devices preventing erase disturb. As described above, 10 V is insufficient to effect an erase disturb condition. Consequently, a selection of applied bias voltage, a segmented source, and/or design of the breakdown voltage for the SGD devices allow sub-blocks within a memory device to be selectively erased while preventing (or at least substantially reducing) an erase disturb of memory cells in non-selected sub-blocks. In this way, selected sub-blocks can be erased at will.

Optimization of breakdown voltages within a device is known independently in the art and may include dopant selection and dopant profiling within the device. Additionally, junctions within the various devices may be formed so that the breakdown voltages are on the various devices may be asymmetric (e.g., the SGD junction on the data line side versus the SGS junction on the source side).

Based on reading and understanding the disclosure provided herein, a person of ordinary skill in the art may readily extend the techniques and concepts to any number and various arrangements of memory cells. For example, the person of ordinary skill in the art can apply the techniques and concepts to a memory block with hundreds, thousands, or even more sub-blocks. Thus, many embodiments may be realized.

For example, a system **500** of FIG. **5** is shown to include a controller **503**, an input/output (I/O) device **511** (e.g., a keypad, a touchscreen, or a display), a memory device **509**, a wireless interface **507**, a static random access memory (SRAM) device **501**, and a shift register **515**, coupled to each other via a bus **513**. A battery **505** may supply power to the system **500** in one embodiment. The memory device **509** may include a NAND memory, a flash memory, a NOR memory, a combination of these, or the like.

The controller **503** may include, for example, one or more microprocessors, digital signal processors, micro-controllers, or the like. The memory device **509** may be used to store information transmitted to or by the system **500**. The memory device **509** may optionally also be used to store information in the form of instructions that are executed by the controller **503** during operation of the system **500** and may be used to store information in the form of user data

either generated, collected, or received by the system **500** (such as image data). The instructions may be stored as digital information and the user data, as disclosed herein, may be stored in one section of the memory as digital information and in another section as analog information. As another example, a given section at one time may be labeled to store digital information and then later may be reallocated and reconfigured to store analog information. The controller **503**, the memory device **509**, and and/or the shift register **515** may include one or more of the novel memory devices described herein.

The I/O device **511** may be used to generate information. The system **500** may use the wireless interface **507** to transmit and receive information to and from a wireless communication network with a radio frequency (RF) signal. Examples of the wireless interface **507** may include an antenna, or a wireless transceiver, such as a dipole antenna. However, the scope of the inventive subject matter is not limited in this respect. Also, the I/O device **511** may deliver a signal reflecting what is stored as either a digital output (if digital information was stored), or as an analog output (if analog information was stored). While an example in a wireless application is provided above, embodiments of the inventive subject matter disclosed herein may also be used in non-wireless applications as well. The I/O device **511** may include one or more of the novel memory devices described herein.

The various illustrations of the methods and apparatuses are intended to provide a general understanding of the structure of various embodiments and are not intended to provide a complete description of all the elements and features of the apparatuses and methods that might make use of the structures, features, and techniques described herein.

The apparatuses of the various embodiments may include or be included in, for example, electronic circuitry used in high-speed computers, communication and signal processing circuitry, single or multi-processor modules, single or multiple embedded processors, multi-core processors, data switches, and application-specific modules including multi-layer, multi-chip modules, or the like. Such apparatuses may further be included as sub-components within a variety of electronic systems, such as televisions, cellular telephones, personal computers (e.g., laptop computers, desktop computers, handheld computers, tablet computers, etc.), workstations, radios, video players, audio players, vehicles, medical devices (e.g., heart monitors, blood pressure monitors, etc.), set top boxes, and various other electronic systems.

A person of ordinary skill in the art will appreciate that, for this and other methods (e.g., erase operations) disclosed herein, the activities forming part of various methods may be implemented in a differing order, as well as repeated, executed simultaneously, with various elements or bias levels substituted one for another. Further, the outlined acts and operations are only provided as examples, and some of the acts and operations may be optional, combined into fewer acts and operations, or expanded into additional acts and operations without detracting from the essence of the disclosed embodiments.

The present disclosure is therefore not to be limited in terms of the particular embodiments described in this application, which are intended as illustrations of various aspects. Many modifications and variations can be made, as will be apparent to a person of ordinary skill in the art upon reading and understanding the disclosure. Functionally equivalent methods and apparatuses within the scope of the disclosure, in addition to those enumerated herein, will be apparent to a person of ordinary skill in the art from the foregoing

descriptions. Portions and features of some embodiments may be included in, or substituted for, those of others. Many other embodiments will be apparent to those of ordinary skill in the art upon reading and understanding the description provided herein. Such modifications and variations are intended to fall within a scope of the appended claims. The present disclosure is to be limited only by the terms of the appended claims, along with the full scope of equivalents to which such claims are entitled. It is also to be understood that the terminology used herein is for the purpose of describing particular embodiments only and is not intended to be limiting.

In various embodiments, an apparatus is provided that includes a block of memory having sub-blocks that share a common data line. Each of the sub-blocks of the block of memory corresponds to a respective one of a number of segmented sources. Each of the segmented sources of the block of memory is electrically isolated from the other segmented sources of the block of memory.

In at least some of the embodiments of the apparatus, the sub-blocks of the block of memory share a number of common access lines. Each of the common access lines corresponds to a respective one of a number of tiers of memory cells in the block of memory.

In at least some of the embodiments of the apparatus, each of the sub-blocks of the block of memory comprises a respective number of strings of memory cells. Each of the strings of memory cells are coupled to the common data line through a respective drain select device and to the respective segmented source through a respective source select device. The source select devices have a higher breakdown voltage than the drain select devices.

In various embodiments, a three-dimensional device is provided that includes multiple tiers of memory cells. The three-dimensional device includes a first sub-block of a block of memory having a first number of memory cell strings and a first segmented source, and a second sub-block of the block of memory having a second number of memory cell strings and a second segmented source. The first and second segmented sources are electrically isolated.

In at least some of the embodiments of the three-dimensional device, each of the first number of memory cell strings is coupled to a respective one of a first number of drain select devices and each of the second number of memory cell strings is coupled to a respective one of a second number of drain select devices.

In at least some of the embodiments of the three-dimensional device, each of the first number of memory cell strings is coupled to a common data line through a respective one of the first number of drain select devices and each of the second number of memory cell strings is coupled to the common data line through a respective one of the second number of drain select devices.

In various embodiments, an apparatus is provided that includes a block of memory having a first sub-block and a second sub-block. The first sub-block and the second sub-block include a first number of memory cell strings and a second number of memory cell strings, respectively. The block of memory further includes a first segmented source coupled to the first number of memory cell strings in the first sub-block through a first number of source select devices, and a second segmented source coupled to the second number of memory cell strings in the second sub-block through a second number of source select devices. The source select devices having a higher breakdown voltage than the drain select devices.

In various embodiments, an electronic device is provided that includes a block of memory having a number of memory cell strings. Each of the memory cell strings including respective memory cells of a number of memory cells. The memory block being divided into a number of sub-blocks, each of the sub-blocks having non-overlapping ones of the memory cell strings. Each of the sub-blocks further includes a respective one of a number of segmented sources. The respective one of the number of segmented sources being coupled to the memory cell strings of the respective sub-block. The segmented sources of the block are electrically isolated from each other. Respective drain select devices are coupled to the memory cell strings of the respective sub-block. Each of the drain select devices has an asymmetric dopant profile.

In at least some of the embodiments of the apparatus, the asymmetric dopant profile is configured to prevent an erase disturb of non-selected ones of the sub-blocks during an erase operation.

As used herein, the term "or" may be construed in an inclusive or exclusive sense. Additionally, although various exemplary embodiments discussed above focus on a 3D NAND memory device, the embodiments are merely given for clarity in disclosure, and thus, are not limited to NAND memory devices or even to memory devices in general.

The Abstract of the Disclosure is provided to comply with 37 C.F.R. §1.72(b), requiring an abstract allowing the reader to quickly ascertain the nature of the technical disclosure. The abstract is submitted with the understanding that it will not be used to interpret or limit the claims. In addition, in the foregoing Detailed Description, it may be seen that various features are grouped together in a single embodiment for the purpose of streamlining the disclosure. This method of disclosure is not to be interpreted as limiting the claims. Thus, the following claims are hereby incorporated into the Detailed Description, with each claim standing on its own as a separate embodiment.

What is claimed is:

1. An apparatus, comprising:

a block of memory including a first sub-block and a second sub-block, the first sub-block and the second sub-block including a first plurality of memory cell strings and a second plurality of memory cell strings, respectively, coupled to a common data line, the block of memory further including a first segmented source coupled to the first plurality of memory cell strings, and a second segmented source coupled to the second plurality of memory cell strings, the first segmented source and the second segmented source being electrically isolated from each other.

2. The apparatus of claim 1, wherein the first sub-block and the second sub-block each share a common source select line.

3. The apparatus of claim 1, further comprising drain select devices coupled to each of the first plurality of memory cell strings and the second plurality of memory cell strings, the drain select devices having an asymmetric dopant profile.

4. The apparatus of claim 3, wherein the drain select devices within the first sub-block are electrically isolated from the drain select devices in the second sub-block.

5. The apparatus of claim 1, wherein the first sub-block and the second sub-block of the block of memory share a plurality of common access lines.

6. The apparatus of claim 1, further comprising a drain select device on a data line side and a source select device

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on a source side coupled to each of the first plurality of memory cell strings and each of the second plurality of memory cell strings, an SGD junction on the data line side having a junction breakdown-voltage that is asymmetric with reference to an SGS junction on the source side.

7. The apparatus of claim 1, wherein the apparatus is configured to apply a first bias voltage to one of the first segmented source and the second segmented source of a sub-block selected to be erased during an erase operation, and apply a second bias voltage to the other segmented source of a sub-block of the block of memory not selected to be erased during the erase operation, the first bias voltage being greater than the second bias voltage.

8. The apparatus of claim 1, wherein the first sub-block and the second sub-block of the block of memory do not share a memory cell.

9. An apparatus, comprising:

a block of memory including a first sub-block and a second sub-block, the first sub-block and the second sub-block including a first plurality of memory cell strings and a second plurality of memory cell strings, respectively, the first plurality of memory cell strings and the second plurality of memory cell strings being coupled to a common data line through a plurality of drain select devices, the block of memory further comprising

a first segmented source coupled to the first plurality of memory cell strings in the first sub-block through a first plurality of source select devices, and

a second segmented source coupled to the second plurality of memory cell strings in the second sub-block through a second plurality of source select devices.

10. The apparatus of claim 9, wherein the first plurality of source select devices and the second plurality of source select devices each have a higher breakdown voltage than each of the plurality of drain select devices.

11. The apparatus of claim 9, wherein the first plurality of memory cell strings and the second plurality of memory cell strings, in the first sub-block and the second sub-block, respectively, are each independently erasable from one another.

12. The apparatus of claim 9, wherein each of the drain select devices has an asymmetric dopant profile.

13. The apparatus of claim 12, wherein the asymmetric dopant profile in the drain select devices is configured to prevent a reverse bias condition in a channel of memory cell strings in one of the sub-blocks that is not selected for an erase operation.

14. An apparatus, comprising:

a block of memory having two or more segmented portions, each of the two or more segmented portions forming separate sub-blocks of the block of memory;

a plurality of memory cells in each of the sub-blocks in the block of memory, the plurality of memory cells being coupled by a common data line, the plurality of memory cells within one sub-block configured to be erasable independently of memory cells in another sub-block; and

a plurality of segmented sources, distinct ones of the plurality of segmented sources each coupled separately to one of the sub-blocks of memory, each of the plurality of segmented sources being electrically isolated from remaining ones of the plurality of segmented sources.

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15. The apparatus of claim 14, wherein each of the plurality of segmented sources is configured to receive a bias level independent of bias levels received by remaining ones of the plurality of segmented sources.

16. The apparatus of claim 14, wherein each of the plurality of memory cells in each of the sub-blocks further includes a source select devices.

17. The apparatus of claim 16, wherein the source select devices in each of the sub-blocks are electrically coupled to one another.

18. The apparatus of claim 14, wherein the sub-blocks are each comprised of non-overlapping portions of the plurality of memory cells.

19. A three-dimensional device, comprising:

a first sub-block and a second sub-block including a first plurality of memory strings and a second plurality of memory strings, respectively, each of the plurality of memory strings including a plurality of memory cells and coupled to a segmented source line, the segmented source line of the first plurality of memory strings and the segmented source line of the second plurality of memory strings being electrically isolated from each other; and

a common data line coupled to the first plurality of memory strings and the second plurality of memory strings.

20. The three-dimensional device of claim 19, wherein the first sub-block and the second sub-block further comprise at least one of segmented access lines and segmented source select lines.

21. The three-dimensional device of claim 20, wherein each of the segmented access lines and the segmented source select lines within the first sub-block are electrically isolated from the segmented access lines and the segmented source select lines within the second sub-block.

22. The three-dimensional device of claim 19, further comprising:

a first segmented source coupled to the first sub-block; and

a second segmented source coupled to the second sub-block.

23. The three-dimensional device of claim 22, wherein the device is configured to apply a bias voltage to the segmented source of a selected one of the sub-blocks that is higher than a bias voltage applied to the segmented source of the non-selected one of the sub-blocks.

24. The three-dimensional device of claim 19, the memory block having common access lines and a common data line coupled to at least the first plurality of memory strings and the second plurality of memory strings.

25. The three-dimensional device of claim 19, wherein the memory block is configured to allow a selected one of the first sub-block and the second sub-block to be erased separately from a non-selected sub-block by a selection of bias voltages applied to segmented drain select lines and segmented source lines within each of the sub-blocks.

26. The three-dimensional device of claim 25, wherein the segmented source line of the selected one of the sub-blocks is configured to have a higher bias voltage applied than a bias voltage applied to the segmented source line of the non-selected one of the sub-blocks.